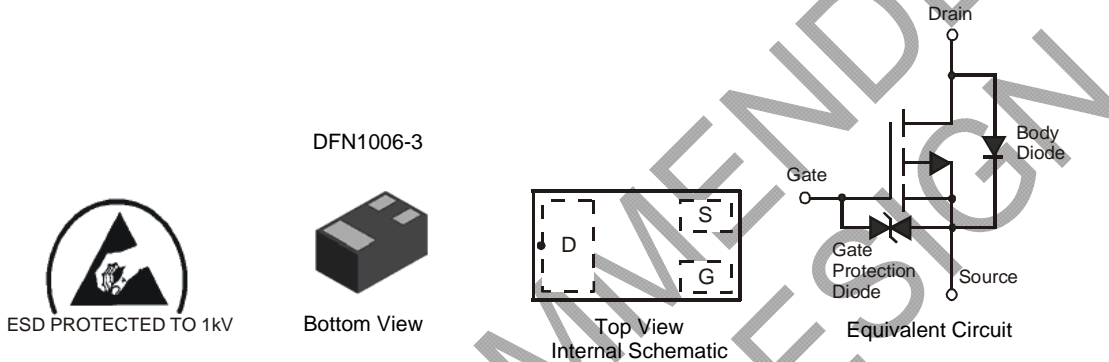


### Features

- Low On-Resistance:
  - $R_{DS(ON)} \leq 6\Omega$  @  $V_{GS} = -4.0V$
  - $R_{DS(ON)} \leq 8\Omega$  @  $V_{GS} = -2.5V$
- Very Low Gate Threshold Voltage,  $\leq 1.0V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Gate, 1KV**
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

### Mechanical Data

- Case: DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.001 grams (approximate)

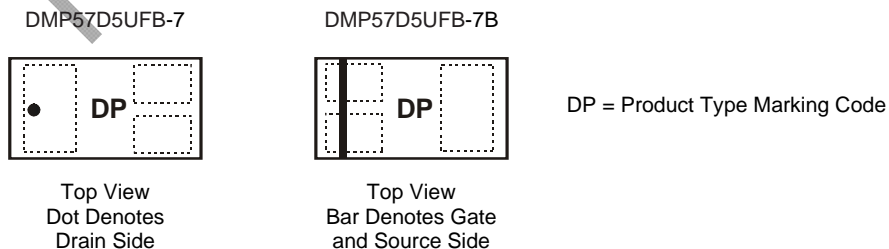


### Ordering Information (Note 3)

| Part Number   | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|---------------|---------|--------------------|-----------------|-------------------|
| DMP57D5UFB-7  | DP      | 7                  | 8               | 3000              |
| DMP57D5UFB-7B | DP      | 7                  | 8               | 10,000            |

- Notes:
1. No purposefully added lead.
  2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
  3. For packaging details, go to our website at <http://www.diodes.com>.

### Marking Information



**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                |        | Symbol           | Value | Units |
|-------------------------------|--------|------------------|-------|-------|
| Drain-Source Voltage          |        | V <sub>DSS</sub> | -50   | V     |
| Gate-Source Voltage           |        | V <sub>GSS</sub> | ±8    | V     |
| Drain Current (Note 4)        | Steady | I <sub>D</sub>   | -200  | mA    |
| Pulsed Drain Current (Note 5) |        | I <sub>DM</sub>  | -700  | mA    |

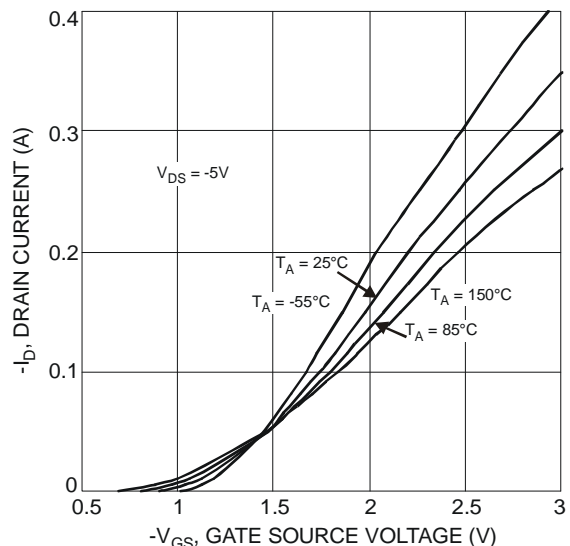
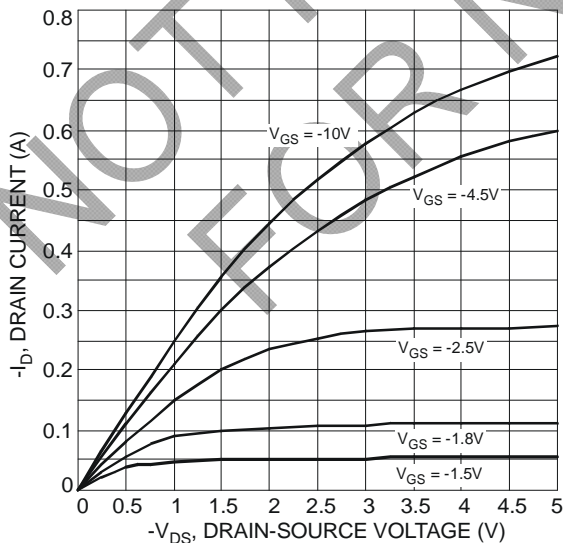
**Thermal Characteristics**

| Characteristic  | Symbol                            | Value       | Units |
|---|-----------------------------------|-------------|-------|
| Total Power Dissipation (Note 4)  | P <sub>D</sub>                    | 425         | mW    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 4) | R <sub>θJA</sub>                  | 294         | °C/W  |
| Operating and Storage Temperature Range                                 | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C    |

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                      | Symbol              | Min  | Typ      | Max    | Unit | Test Condition  |
|-------------------------------------|---------------------|------|----------|--------|------|---|
| <b>OFF CHARACTERISTICS (Note 6)</b> |                     |      |          |        |      |   |
| Drain-Source Breakdown Voltage      | BV <sub>DSS</sub>   | -50  | —        | —      | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA   |
| Zero Gate Voltage Drain Current     | I <sub>DSS</sub>    | —    | —        | -10    | μA   | V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V  |
| Gate-Source Leakage                 | I <sub>GSS</sub>    | —    | —        | ±500   | nA   | V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V   |
| <b>ON CHARACTERISTICS (Note 6)</b>  |                     |      |          |        |      |   |
| Gate Threshold Voltage              | V <sub>GS(th)</sub> | -0.7 | —        | -1.0   | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA   |
| Static Drain-Source On-Resistance   | R <sub>DS(ON)</sub> | —    | 4.6<br>6 | 6<br>8 | Ω    | V <sub>GS</sub> = -4.0V, I <sub>D</sub> = -100mA<br>V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -80mA |
| Forward Transfer Admittance         | Y <sub>fs</sub>     | 100  | —        | —      | mS   | V <sub>DS</sub> = -5V, I <sub>D</sub> = -100mA  |
| Diode Forward Voltage (Note 6)      | V <sub>SD</sub>     | —    | —        | -1.2   | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = -100mA   |
| <b>DYNAMIC CHARACTERISTICS</b>      |                     |      |          |        |      |   |
| Input Capacitance                   | C <sub>iss</sub>    | —    | 29       | —      | pF   |   |
| Output Capacitance                  | C <sub>oss</sub>    | —    | 7.3      | —      | pF   | V <sub>DS</sub> = -4V, V <sub>GS</sub> = 0V   |
| Reverse Transfer Capacitance        | C <sub>rss</sub>    | —    | 2.5      | —      | pF   | f = 1.0MHz  |

- Notes: 4. Device mounted on FR-4 PCB. t ≤ 5 sec.  
 5. Pulse width ≤ 10μs, Duty Cycle ≤ 1%.  
 6. Short duration pulse test used to minimize self-heating effect.



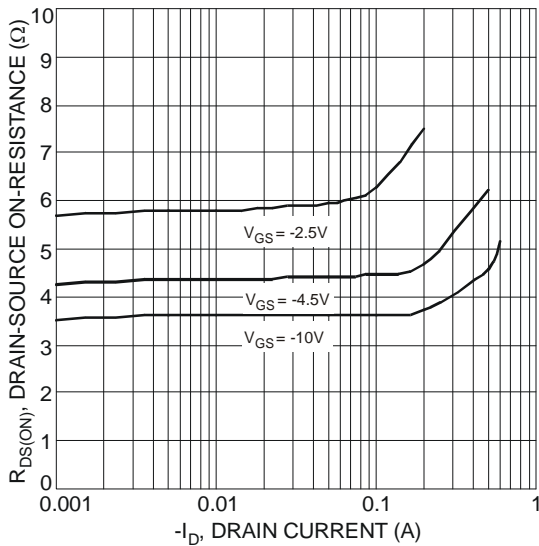


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

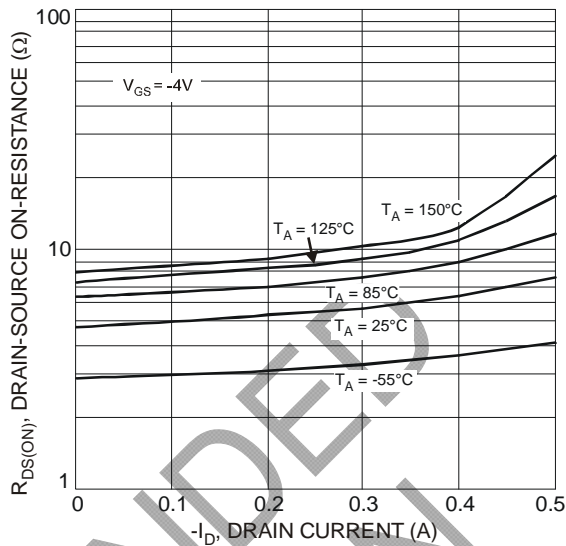


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

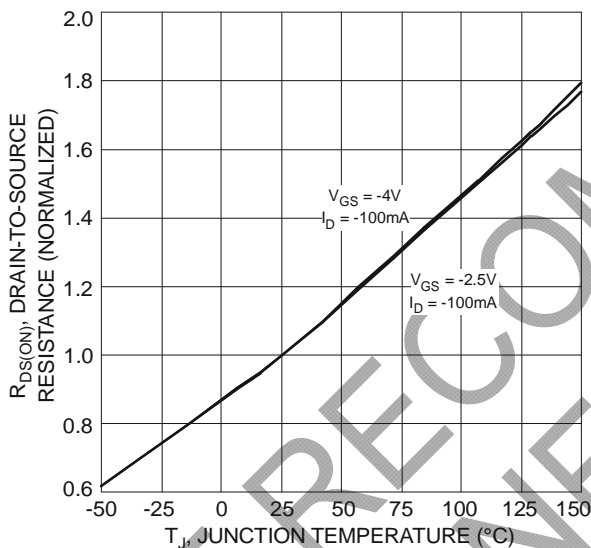


Fig. 5 On-Resistance Variation with Temperature

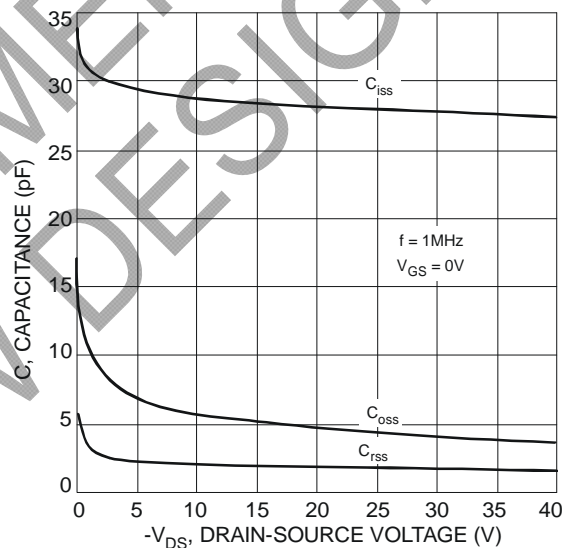


Fig. 6 Typical Capacitance

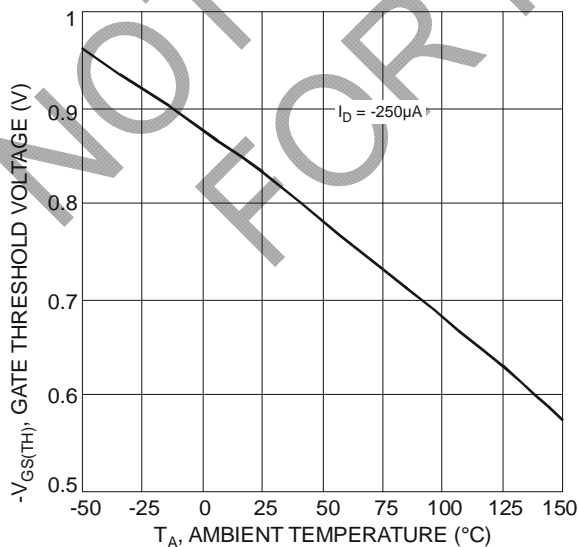


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

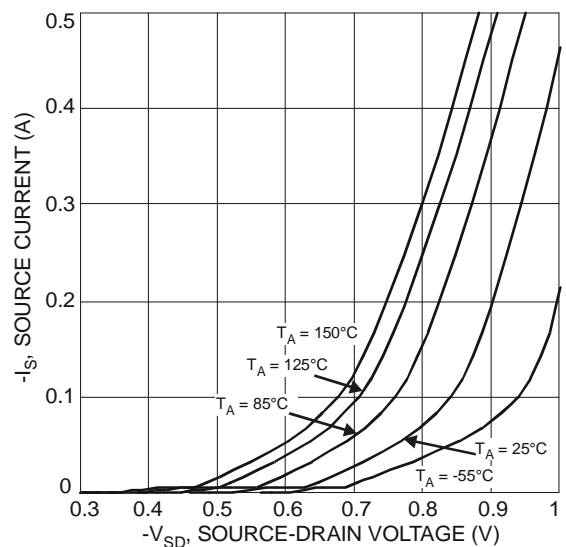


Fig. 8 Diode Forward Voltage vs. Current

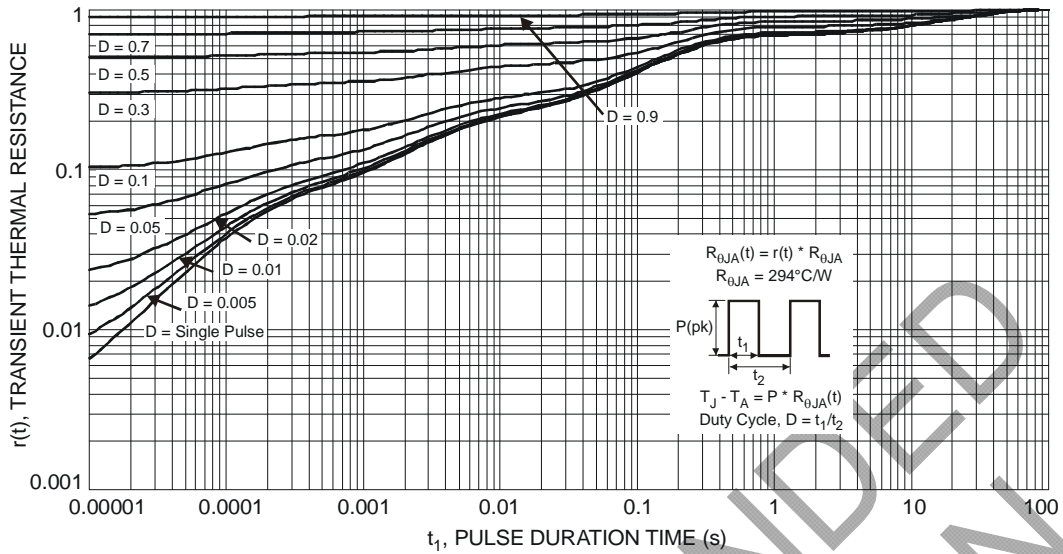
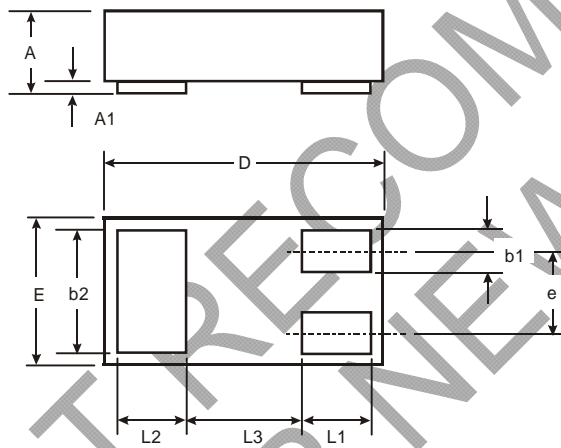


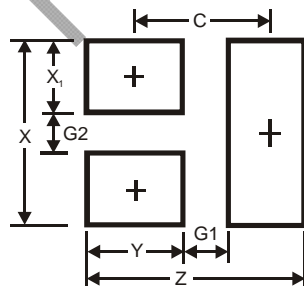
Fig. 9 Transient Thermal Response

**Package Outline Dimensions**



| DFN1006-3            |      |       |      |
|----------------------|------|-------|------|
| Dim                  | Min  | Max   | Typ  |
| A                    | 0.47 | 0.53  | 0.50 |
| A1                   | 0    | 0.05  | 0.03 |
| b1                   | 0.10 | 0.20  | 0.15 |
| b2                   | 0.45 | 0.55  | 0.50 |
| D                    | 0.95 | 1.075 | 1.00 |
| E                    | 0.55 | 0.675 | 0.60 |
| e                    | —    | —     | 0.35 |
| L1                   | 0.20 | 0.30  | 0.25 |
| L2                   | 0.20 | 0.30  | 0.25 |
| L3                   | —    | —     | 0.40 |
| All Dimensions in mm |      |       |      |

**Suggested Pad Layout**



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 1.1           |
| G1         | 0.3           |
| G2         | 0.2           |
| X          | 0.7           |
| X1         | 0.25          |
| Y          | 0.4           |
| C          | 0.7           |

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